NPN Triple Diffused Planar Silicon Transistor



2SC4459

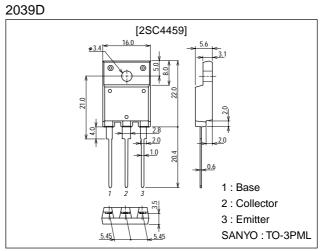
# **500V/10A Switching Regulator Applications**

### Features

- $\cdot$  High breakdown voltage, high reliability.
- · Fast switching speed.
- · Wide ASO.
- · Adoption of MBIT process.
- · Micaless package facilitating mounting.

## Package Dimensions

unit:mm



# **Specifications**

### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CBO</sub>		800	V
Collector-to-Emitter Voltage	VCEO		500	V
Emitter-to-Base Voltage	VEBO		7	V
Collector Current	I <sub>C</sub>		10	А
Collector Current (Pulse)	ICP	PW≤300µs, duty cycle≤10%	20	А
Base Current	Ι <sub>Β</sub>		3	А
Collector Dissipation	PC		3	W
		Tc=25°C	50	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V <sub>CB</sub> =500V, I <sub>E</sub> =0			10	μΑ
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =5V, I <sub>C</sub> =0			10	μΑ
DC Current Gain	hFE1	V <sub>CE</sub> =5V, I <sub>C</sub> =0.8A	15*		50*	
	h <sub>FE</sub> 2	$V_{CE}=5V, I_{C}=4A$	8			

\* : For the hFE1 of the 2SC4459, specify two ranks or more in principle.

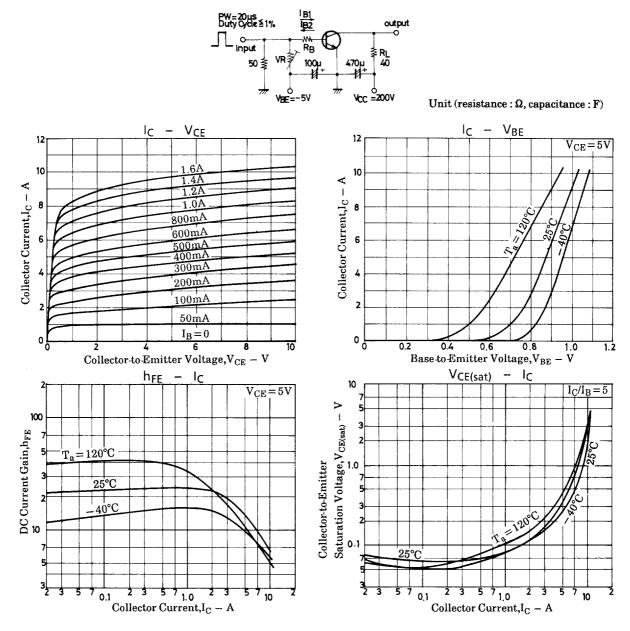
15 L 30 20 M 40 30 N 50

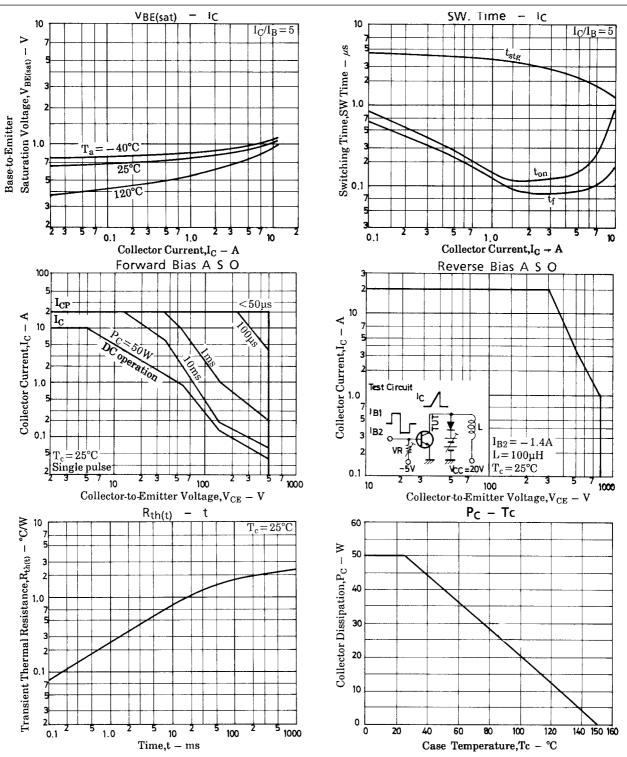
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Parameter	Symbol	Conditions		Ratings		
			min	typ	max	Unit
Gain-Bandwidth Product	fT	V <sub>CE</sub> =10V, I <sub>C</sub> =0.8A		18		MHz
Output Capacitance	Cob	V <sub>CB</sub> =10V, f=1MHz		50		pF
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =4A, I <sub>B</sub> =0.8A			1.0	V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =4A, I <sub>B</sub> =0.8A			1.5	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=1mA, IE=0	800			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =5mA, R <sub>BE</sub> =∞	500			V
Emitter-to-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =1mA, I <sub>C</sub> =0	7			V
Collector-to-Emitter Sustain Voltage	V <sub>CEX(sus)</sub>	I <sub>C</sub> =3.5A, I <sub>B1</sub> =-I <sub>B2</sub> =1.4A, L=500µH, Clamped	500			V
Turn-ON Time	ton	$V_{CC}$ =200V, 5I <sub>B1</sub> =-2.5I <sub>B2</sub> =I <sub>C</sub> =5A, R <sub>L</sub> =40 $\Omega$			0.5	μs
Storage Time	tstg	$V_{CC}$ =200V, 5I <sub>B1</sub> =-2.5I <sub>B2</sub> =I <sub>C</sub> =5A, R <sub>L</sub> =40 $\Omega$			3.0	μs
Fall Time	tf	V <sub>CC</sub> =200V, 5I <sub>B1</sub> =-2.5I <sub>B2</sub> =I <sub>C</sub> =5A, R <sub>L</sub> =40Ω			0.3	μs

### Switching Time Test Circuit





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